# **DISCRETE SEMICONDUCTORS**

# DATA SHEET

# BYC10-600CT Dual rectifier diode ultrafast, low switching loss

**Product specification** 

March 2001



**NXP Semiconductors Product specification** 

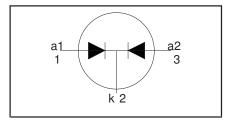
# Rectifier diode ultrafast, low switching loss

**BYC10-600CT** 

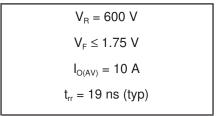
# **FEATURES**

- Dual diode
- · Extremely fast switching
- · Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

# **SYMBOL**



# **QUICK REFERENCE DATA**



# **APPLICATIONS**

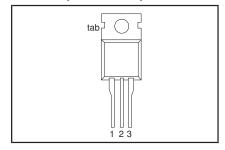
- Active power factor correction
- Half-bridge lighting ballasts Half-bridge/ full-bridge switched mode power supplies.

The BYC10-600CT is supplied in the SOT78 (TO220AB) conventional leaded package.

# **PINNING**

PIN	PIN DESCRIPTION	
1	anode 1	
2	cathode	
3	anode 2	
tab	cathode	

# **SOT78 (TO220AB)**



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	Peak repetitive reverse voltage			600	V
V <sub>RWM</sub>	Crest working reverse voltage		-	600	l v l
V <sub>R</sub>	Continuous reverse voltage	T <sub>mb</sub> ≤ 110 °C	-	500	V
I <sub>O(AV)</sub>	Average output current (both	$\delta = 0.5$ ; with reapplied $V_{RRM(max)}$ ;	-	10	Α
(7,11)	diodes conducting)	$ T_{mb}  < 50  ^{\circ}C^{1}$			
I <sub>FRM</sub>	Repetitive peak forward current	$\delta = 0.5$ ; with reapplied $V_{PPM(max)}$ ;	-	10	A
11100	per diode	$T_{mb} \le 50  ^{\circ}C^1$			
I <sub>FSM</sub>	Non-repetitive peak forward	t = 10 ms	-	40	A
1 0.00	current per diode	t = 8.3 ms	-	44	A
	· ·	sinusoidal; T <sub>i</sub> = 150°C prior to surge			
		with reapplied V <sub>RWM(max)</sub>			
T <sub>stg</sub>	Storage temperature	1 1 Tarivi(max)	-40	150	°C
T <sub>i</sub>	Operating junction temperature		-	150	°C

# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	mounting base	per diode both diodes in free air.	- - -	- - 60	2.5 2.2 -	K/W K/W K/W

 $<sup>\</sup>mathbf{1} T_{mb(max)}$  limited by thermal runaway

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# **ELECTRICAL CHARACTERISTICS**

T<sub>i</sub> = 25 °C, per diode unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage	I <sub>F</sub> = 5 A; T <sub>i</sub> = 150°C	-	1.4	1.75	V
		$I_F = 10 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	1.75	2.2	V
1	Reverse current	$I_F = 5 \text{ A};$ $V_R = 600 \text{ V}$	-	2.0 9	2.9 100	V μA
I <sub>R</sub>	Theverse current	$V_R = 500 \text{ V}; T_j = 100 \text{ °C}$	-	0.9	3.0	mA
t <sub>rr</sub>	Reverse recovery time	$I_{\rm F} = 1 \text{ A}; V_{\rm B} = 30 \text{ V}; dI_{\rm F}/dt = 50 \text{ A/}\mu\text{s}$	-	30	50	ns
t <sub>rr</sub>	Reverse recovery time	$I_F = 5 \text{ A}; V_R = 400 \text{ V};$	-	19	-	ns
t <sub>rr</sub>	Reverse recovery time	$dI_F/dt = 500 \text{ A/}\mu\text{s}$ $I_F = 5 \text{ A}; V_R = 400 \text{ V};$ $dI_F/dt = 500 \text{ A/}\mu\text{s}; T_j = 100 ^{\circ}\text{C}$	-	25	30	ns
I <sub>rrm</sub>	Peak reverse recovery current	I <sub>F</sub> = 5 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 50 A/μs; T <sub>i</sub> = 125°C	-	0.7	3	А
I <sub>rrm</sub>	Peak reverse recovery current	$d_{I_F}/dt = 50 \text{ A/}\mu\text{s}, \ T_i = 125 \text{ C}$ $I_F = 5 \text{ A}; \ V_R = 400 \text{ V};$ $d_{I_F}/dt = 500 \text{ A/}\mu\text{s}; \ T_j = 125 ^{\circ}\text{C}$	-	8	11	А
$V_{fr}$	Forward recovery voltage	$I_F = 10 \text{ A}; dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	9	11	V

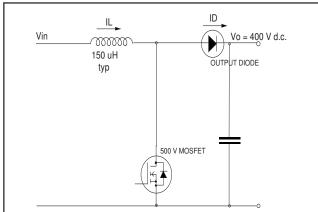


Fig. 1. Typical application, output rectifier in boost converter power factor correction circuit. Continuous conduction mode, where the transistor turns on whilst forward current is still flowing in the diode.

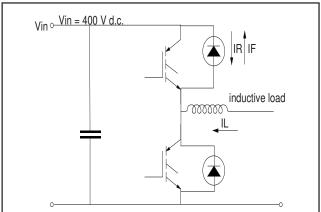


Fig.2. Typical application, freewheeling diode in half bridge converter. Continuous conduction mode, where each transistor turns on whilst forward current is still flowing in the other bridge leg diode.

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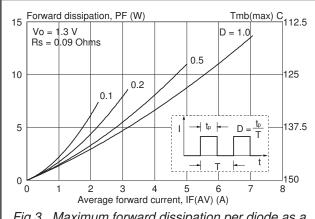


Fig.3. Maximum forward dissipation per diode as a function of average forward current; rectangular current waveform where  $I_{F(AV)} = I_{F(BMS)} \times \sqrt{D}$ .

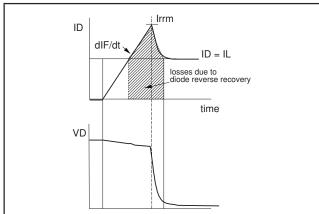


Fig.6. Origin of switching losses in transistor due to diode reverse recovery.

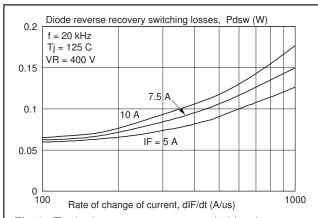


Fig.4. Typical reverse recovery switching losses per diode, as a function of rate of change of current  $dl_{\it F}/dt$ .

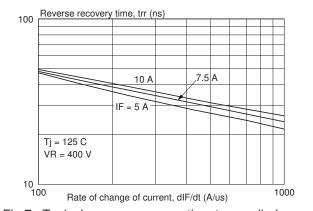


Fig.7. Typical reverse recovery time t<sub>rr</sub>, per diode as a function of rate of change of current dl<sub>r</sub>/dt.

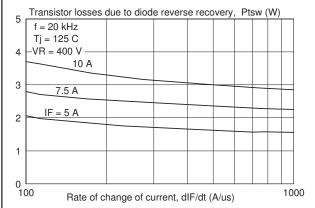


Fig.5. Typical switching losses in transistor due to reverse recovery of diode, as a function of of change of current dl<sub>r</sub>/dt.

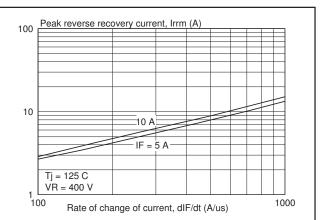


Fig.8. Typical peak reverse recovery current per diode,  $I_{rrm}$  as a function of rate of change of current  $dI_{e}/dt$ .

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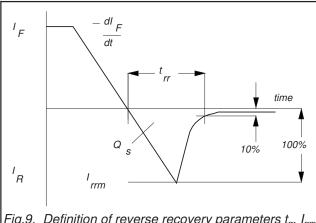


Fig.9. Definition of reverse recovery parameters  $t_{rr}$ ,  $l_{rrm}$ 

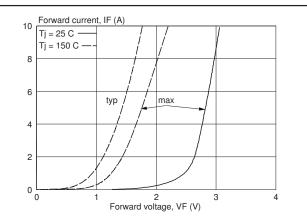


Fig.12. Typical and maximum forward characteristic per diode,  $I_F = f(V_F)$ ;  $T_i = 25^{\circ}C$  and  $150^{\circ}C$ .

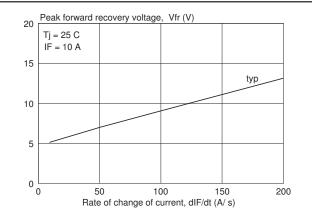


Fig.10. Typical forward recovery voltage per diode,  $V_{tt}$  as a function of rate of change of current  $dI_F/dt$ .

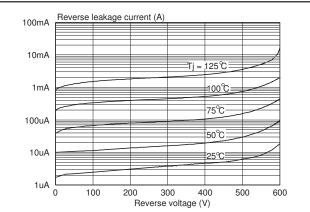
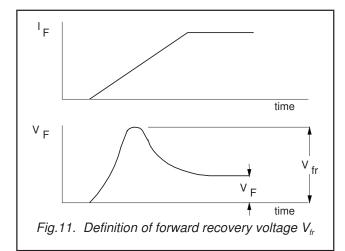
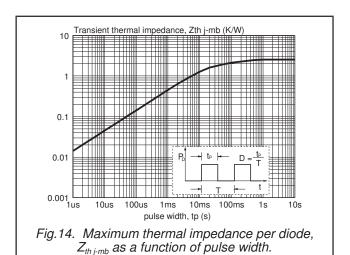


Fig.13. Typical reverse leakage current per diode as a function of reverse voltage.  $I_R = f(V_R)$ ; parameter  $T_i$ 

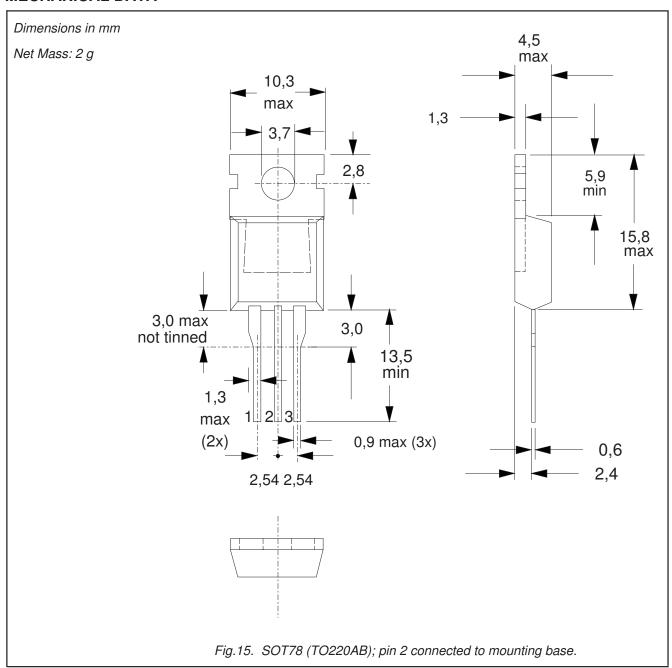




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# **MECHANICAL DATA**



- Refer to mounting instructions for SOT78 (TO220) envelopes.
   Epoxy meets UL94 V0 at 1/8".

# Legal information

### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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